

UNISONIC TECHNOLOGIES CO., LTD

UT3458 Preliminary Power MOSFET

4.1 A, 60 V (D-S) N-CHANNEL POWER MOSFET

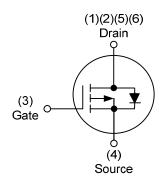
■ DESCRIPTION

The UTC **UT3458** is N-channel enhancement mode power MOSFET using UTC's advanced technology to provide the customers with perfect $R_{\rm DS(ON)}$ and low gate charge. This device can be operated with 4.5V low gate voltage.

■ FEATURES

- * V_{DS}=60V
- * I_D =4.1A
- * $R_{DS(ON)}$ =0.1 Ω @ V_{GS} =10V, $R_{DS(ON)}$ =0.128 Ω @ V_{GS} =4.5V

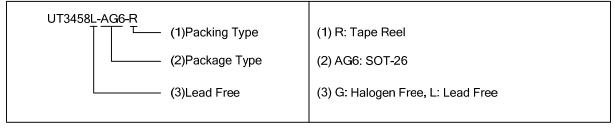
■ SYMBOL



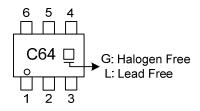


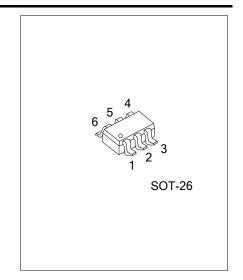
| Orderin | g Number | Dookogo | | Р | in Ass | ignmeı | nt | | Dooking | |
|---------------|---------------|---------|---|---|--------|--------|----|---|-----------|--|
| Lead Free | Halogen Free | Package | 1 | 2 | 3 | 4 | 5 | 6 | Packing | |
| UT3458L-AG6-R | UT3458L-AG6-R | SOT-26 | D | D | G | S | D | D | Tape Reel | |

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING





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■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

| ı | PARAMETER | SYMBOL | RATINGS | UNIT | |
|----------------------|----------------------------------|------------------|----------|------|--|
| Drain-Source Voltage | ge | V _{DSS} | 60 | V | |
| Gate-Source Voltag | e | V_{GSS} | ±20 | V | |
| _ | Continuous T _A =25°C | , | 4.1 | Α | |
| Drain Current | (Note 2, 3) T _A =70°C | l _D | 3.2 | Α | |
| | Pulsed | I _{DM} | 15 | Α | |
| Power Dissipation (I | Note 2, 3) | P _D | 2 | W | |
| Junction Temperature | | TJ | +150 | °C | |
| Storage Temperatur | re | T _{STG} | -55~+150 | °C | |

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Surface Mounted on FR4 Board.
- 3. t≤5 sec

■ THERMAL CHARACTERISTICS

| PARAMETER | SYMBOL | RATINGS | UNIT |
|------------------------------|---------------|---------|------|
| Junction to Ambient (Note 2) | θ_{JA} | 62.5 | °C/W |

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise noted)

| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------------------------------------|---------|---------------------|--------------------------------------------------------------------|-----|-------|-------|------|
| OFF CHARACTERISTICS | | | | | | | |
| Drain-Source Breakdown Voltage | | BV _{DSS} | I _D =250μA, V _{GS} =0V | 60 | | | V |
| Drain-Source Leakage Current | | I _{DSS} | V _{DS} =48V, V _{GS} =0V | | | 1 | μA |
| Gate- Source Leakage Current Reverse | | I _{GSS} | V _{GS} =+20V, V _{DS} =0V | | | +100 | nA |
| | | | V _{GS} =-20V, V _{DS} =0V | | | -100 | nA |
| ON CHARACTERISTICS | | | | | | | |
| Gate Threshold Voltage | | $V_{GS(TH)}$ | V _{DS} =V _{GS} , I _D =250μA | 1.5 | | 3 | V |
| Static Drain-Source On-State Resistance | | R _{DS(ON)} | V _{GS} =10V, I _D =3.2A | | 0.082 | 0.1 | Ω |
| | | | V _{GS} =4.5V, I _D =2.8A | | 0.105 | 0.128 | Ω |
| On State Drain Current | | I _{D(ON)} | V _{GS} =10V, V _{DS} =5V | 10 | | | Α |
| SWITCHING PARAMETERS | • | , , | | | | • | |
| Input Capacitance | | C _{ISS} | | | 350 | | |
| Output Capacitance | | Coss | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{V}, f = 1 \text{MHz}$ | | 40 | | ₽F |
| Reverse Transfer Capacitance | | C_{RSS} | | | 20 | | |
| Total Gate Charge | | Q_{G} | V _{DS} =10V, V _{DS} =48V, I _D =3.2A | | 7.1 | 11 | |
| | | | V _{DS} =4.5V, V _{DS} =48V, I _D =3.2A | | 3.5 | 5.5 | |
| Gate to Source Charge | | Q _{GS} | Vps=4.5V, Vps=48V, Ip=3.2A | | 1.1 | | nC |
| Gate to Drain Charge | | Q_{GD} | -V _{DS} -4.5V, V _{DS} -48V, I _D -3.2A | | 0.95 | | |
| Turn-ON Delay Time | | t _{D(ON)} | | | 16 | 25 | |
| Rise Time | | t _R | V _{DD} =30V, I _D ≈2.5A, R _L =12Ω, | | 17 | 30 | |
| Turn-OFF Delay Time | | t _{D(OFF)} | V_{GEN} =4.5V, R_{G} =1 Ω (Note 1, 2) | | 12 | 20 | |
| Fall Time | | t _F | | | 10 | 15 | |
| Turn-ON Delay Time | | t _{D(ON)} | | | 5 | 10 | ns |
| Rise Time | | t _R | V _{DD} =30V, I _D ≈2.5A, R _L =12Ω, | | 12 | 20 | |
| Turn-OFF Delay Time | | t _{D(OFF)} | V _{GEN} =10V, R _G =2.5Ω(Note 1, 2) | | 18 | 30 | |
| Fall Time | | t _F | | | 10 | 15 | |
| SOURCE- DRAIN DIODE RATINGS | S AND C | CHARACTER | ISTICS | | | • | |
| Maximum Body-Diode Continuous Current | | Is | | | | 2.9 | Α |
| Maximum Body-Diode Pulsed Curre | nt | I _{SM} | | | | 10 | Α |
| Drain-Source Diode Forward Voltage | | V_{SD} | I _S =2.5A, V _{GS} =0V | | 0.8 | 1.2 | V |
| Body Diode Reverse Recovery Time | 9 | t _{RR} | I _F =2.5A, di/dt=100A/μs (Note 1) | | 25 | 50 | ns |

Notes: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle ≤ 2%

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^{2.} Guaranteed by design, not subject to production testing.